SiA472EDJ

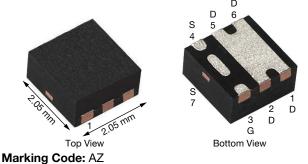
www.vishay.com

Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^a	Q _g (TYP.)			
30	0.0200 at V_{GS} = 4.5 V	12	11.6 nC			
	0.0263 at V _{GS} = 2.5 V	12	11.0110			

PowerPAK[®] SC-70-6L Single



Ordering Information:

SiA472EDJ-T1-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- TrenchFET[®] Power MOSFET
- Thermally enhanced PowerPAK[®] SC-70 package - Small footprint area
- Typical ESD performance 2500 V HBM
- 100 % $R_{\rm q}$ and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

Boost converters

DC/DC converters

- · Load switch, OVP switch
 - GO

N-Channel MOSFET Οs

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 12	V	
	T _C = 25 °C		12 ^a		
Continuous Duois Connect (T. 150 °C)	T _C = 70 °C	Ι. Γ	12 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	11 ^{b, c}		
	T _A = 70 °C	1 [8.8 ^{b, c}		
Pulsed Drain Current (t = 300 µs)		I _{DM}	30	— A	
Octation of Octation Device Diverse Octation	T _C = 25 °C		12 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.9 ^{b, c}		
Avalanche Current		I _{AS}	15		
Single Pulse Avalanche L = 0.1 mH		E _{AS}	11.25	mJ	
	T _C = 25 °C		19.2		
Martin an Dan an Disabartina	T _C = 70 °C		12.3		
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	W	
	T _A = 70 °C	1	2.2 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		
Soldering Recommendations (Peak Temperature) d, e			260	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	0/00	

Notes

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

Maximum under steady state conditions is 80 °C/W. f.

1

RoHS COMPLIANT HALOGEN FREE

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		•				
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA	30	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	34	-	mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-3.8	-	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.6	-	1.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$	-	-	± 15	μA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	- μΑ
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	-	-	10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	20	-	-	А
	_	V _{GS} = 4.5 V, I _D = 10.8 A	-	0.0167	0.0200	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 9.4 A	-	0.0200	0.0263	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 11 A	-	50	-	S
Dynamic ^b		•				
Input Capacitance	C _{iss}		-	1265	-	pF
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	-	132	-	
Reverse Transfer Capacitance	C _{rss}		-	80	-	
	Qg	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	24	36	nC
Total Gate Charge			-	11.6	17.4	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	2.9	-	
Gate-Drain Charge	Q _{gd}		-	2.2	-	
Gate Resistance	R _g	f = 1 MHz	0.6	3.3	6.6	Ω
Turn-On Delay Time	t _{d(on)}		-	10	15	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, \text{ R}_{L} = 1.7 \Omega$	-	23	35	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 8.6$ A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	26	39	
Fall Time	t _f		-	9	18	
Turn-On Delay Time	t _{d(on)}		-	4	8	ns
Rise Time	t _r	$V_{DD} = 15 \text{ V}, \text{ R}_{\text{L}} = 1.7 \Omega$	-	14	21	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 8.6 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$	-	25	38	
Fall Time	t _f		-	9	18	
Drain-Source Body Diode Characteristic	s	·				
Continuous Source-Drain Diode Current	IS	T _C = 25 °C	-	-	12	•
Pulse Diode Forward Current	I _{SM}	-		-	30	A
Body Diode Voltage	V _{SD}	$I_{\rm S} = 8.6$ A, $V_{\rm GS} = 0$ V	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}		-	15	23	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	7	14	nC
Reverse Recovery Fall Time	t _a	I _F = 8.6 A, dl/dt = 100 A/μs, T _J = 25 °C		9	-	ns
Reverse Recovery Rise Time	t _b			6	-	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

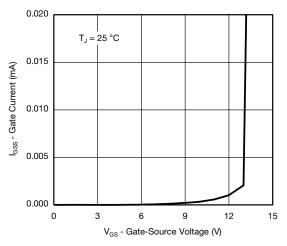
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

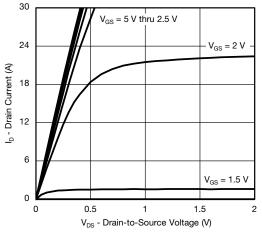


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Gate Current vs. Gate-Source Voltage





 $V_{GS} = 4.5 V$

24

30

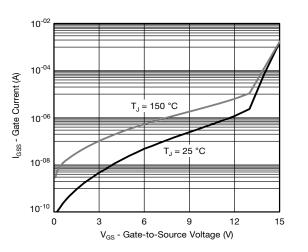
 $V_{GS} = 2.5 V$

12

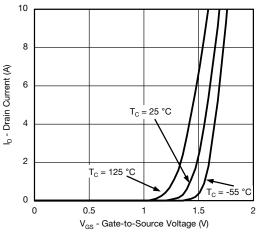
18

I_D - Drain Current (A)

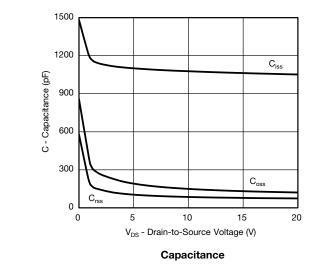
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-Source Voltage



Transfer Characteristics



S16-0048-Rev. A, 18-Jan-16

6

0.030

0.024

0.018

0.012

0.006

0

 $R_{DS(on)}$ - On-Resistance (Ω)

3

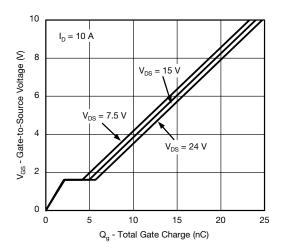
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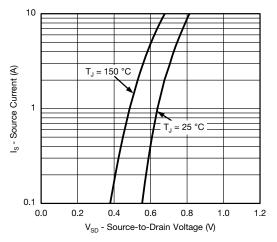


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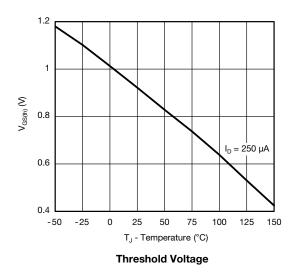
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

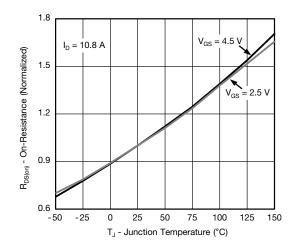


Gate Charge

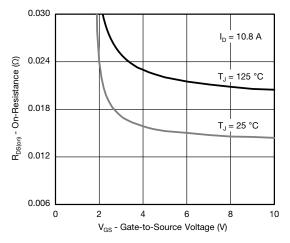


Source-Drain Diode Forward Voltage

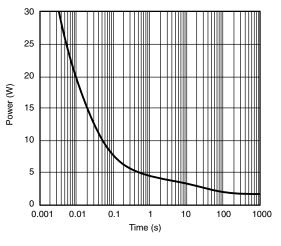




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient)

S16-0048-Rev. A, 18-Jan-16

4

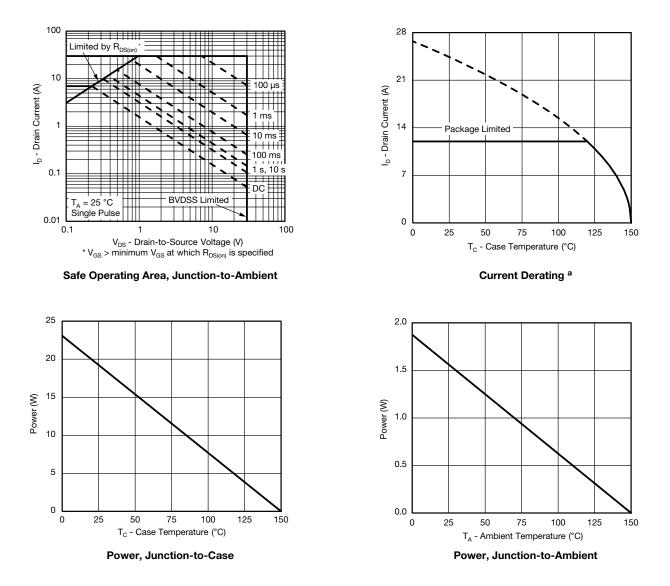
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Note

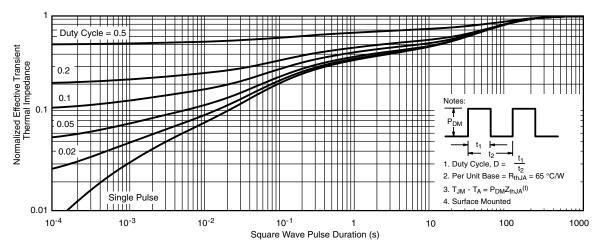
a. The power dissipation P_D is based on T_J (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



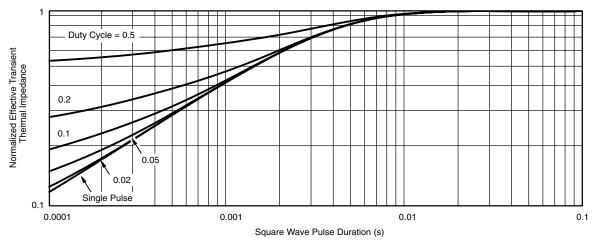
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

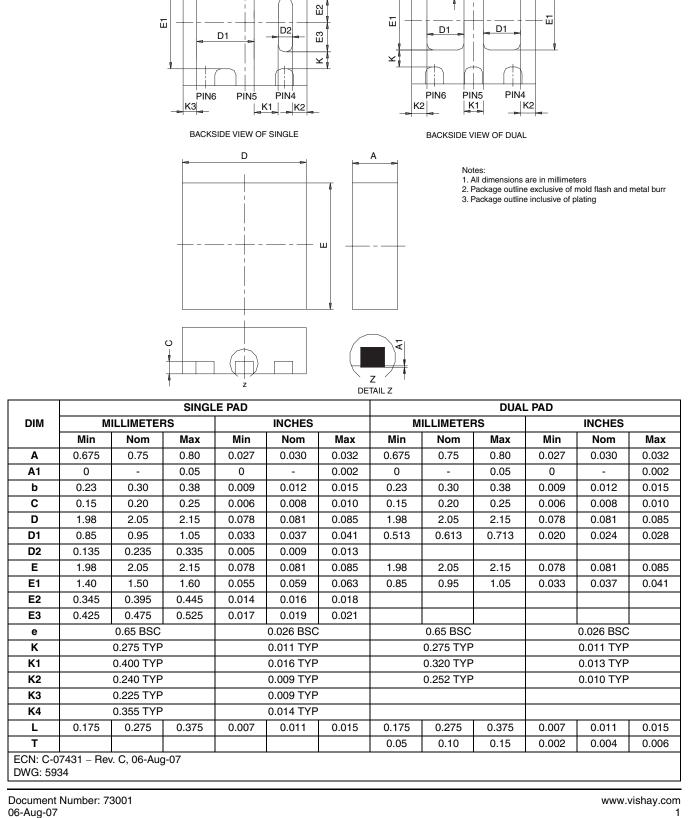


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67554.



PowerPAK[®] SC70-6L

b PIN2 PIN1 PIN3 _ ₹

Package Information

b

PIN3

__ ₿

PIN2

PIN1

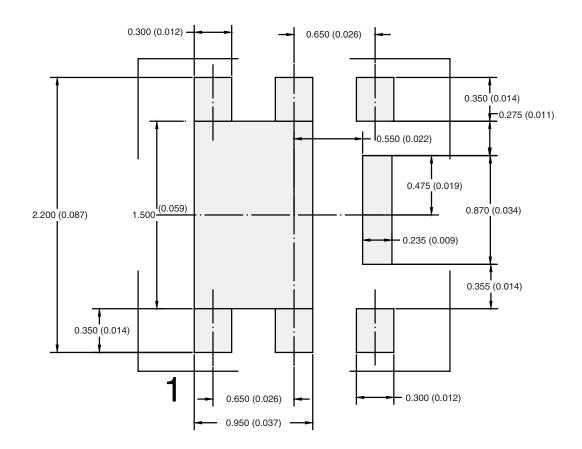
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RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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APPLICATION NOTE



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